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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/709,307	04/28/2004	Ming-Dou Ker	12053-US-PA	3306

31561 7590 12/29/2005

JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE
7 FLOOR-1, NO. 100
ROOSEVELT ROAD, SECTION 2
TAIPEI, 100
TAIWAN

EXAMINER	
CHIU, TSZ K	

ART UNIT	PAPER NUMBER
2822	

DATE MAILED: 12/29/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/709,307	KER ET AL.	
	Examiner	Art Unit	
	Tsz K. Chiu	2822	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 2 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *28 April 2004*.

2a)☐ This action is **FINAL**. 2b)☒ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *1-13* is/are pending in the application.

4a) Of the above claim(s) *7-13* is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☐ Claim(s) _____ is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☒ The specification is objected to by the Examiner.

10)☒ The drawing(s) filed on *28 April 2004* is/are: a)☐ accepted or b)☒ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☒ All b)☐ Some * c)☐ None of:

1.☒ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☒ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____ .
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

DETAILED ACTION

Drawings

The drawings are objected to because in page 5, lines 14 of the specification is said that "a fourth N+ diffusion area, partially formed in the third N-well region..." and "a fifth N+ diffusion, partially formed in the third N-well region". If both 4^{th} and 5^{th} N+ diffusion region are formed on the third N-well region the second N-well region will have no N+ diffusion on there and that doesn't match the figure 2A or 2B in the application. Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Claim Objections

Claim 1 is objected to because of the following informalities: Page 2, Lines 1 of the amendment claim, where said "a fifth N+ diffusion, partially formed in the third N-well region..." should be a fifth N+ diffusion, partially formed in the ***second*** N-well region... Appropriate correction is required.

Allowable Subject Matter

The following is an examiner's statement of reasons for allowance:

The cited art of record fails to teach an double triggered silicon controlling rectifier having a first N-well region, formed within the P-type substrate; a second N-well region, formed on one side of the first N-well region; a third N-well region, on another side of the first N-well region, opposite to the second N-well region; a plurality of N+ diffusion areas, with a first N+ diffusion area, formed in the first N-well region and coupled to an external power terminal; a second N+ diffusion area, formed in the first N-well region and on one side of the first N+ diffusion area,; a third N+ diffusion area, formed in the first N-well region and on another side of the first N+ diffusion area, opposite to the second N+ diffusion area; a fourth N+ diffusion area, partially formed in the third N-well region and partially formed in the P-type substrate, and on one side of the second N+ diffusion region, opposite to the first N+ diffusion region as a cathode of the double-triggered silicon controlling rectifier; and a fifth N+ diffusion, partially formed in the ***second*** N-well region and partially formed in the P-type substrate, and on one side of the third N+ diffusion region, opposite to the first N+ diffusion region as the cathode of the double-triggered silicon controlling rectifier; a plurality of P+ diffusion areas, with a first P+ diffusion area, formed within the first N-well region and between

the first and the second N+ diffusion area,; a second P+ diffusion area, formed within the first N-well region and between the first and the third N+ diffusion area; a third P+ diffusion area, formed within the P-type substrate between the first and the third N-well regions, and between the second and the fourth N+ diffusion areas, as a P-type trigger terminal of the double-triggered silicon controlling rectifier; a fourth P+ diffusion area, formed within the P-type substrate between the first and the second N-well regions, and between the third and the fifth N+ diffusion areas, as the P-type trigger terminal of the double-triggered silicon controlling rectifier; a fifth P+ diffusion area, formed within the P-type substrate and on one side of the fourth N+ diffusion area, opposite to the third P+ diffusion area, as a ground terminal of the double-triggered silicon controlling rectifier; and a sixth P+ diffusion area, formed within the P-type substrate and on one side of the fifth N+ diffusion area, opposite to the fourth P+ diffusion area, as the ground terminal of the double-triggered silicon controlling rectifier; and a plurality of isolation structures, formed within the P-type substrate and between spaces of the pluralities of N+ and P+ diffusion areas. Therefore, claims 1-6 are presently allowed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

This application is in condition for allowance except for the following formal matters:

In claim 1 "a fifth N+ diffusion, partially formed in the third N-well region..." should be a fifth N+ diffusion, partially formed in the ***second*** N-well region.

Also in the specification paragraph 10, page 5, lines 14 where said "a fifth N+ diffusion, partially formed in the third N-well region..." should be a fifth N+ diffusion, partially formed in the ***second*** N-well region.

Prosecution on the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

A shortened statutory period for reply to this action is set to expire **TWO MONTHS** from the mailing date of this letter.

Inquiry

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tsz K. Chiu whose telephone number is 517-272-8656. The examiner can normally be reached on 0800 to 1700.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra V. Smith can be reached on 571-272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TKC
December 14, 2005

ZANDR[illegible]ITH
PRIMARY EXAMINER
23 Dec. 2005